

ZXMP3A16N8

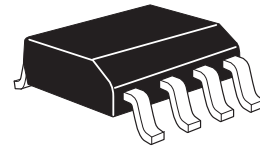
30V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -30V$; $R_{DS(ON)} = 0.040\Omega$; $I_D = -6.7A$

DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



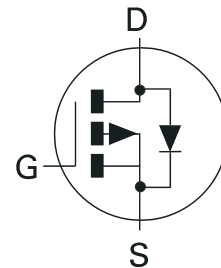
SO8

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- Disconnect switches
- Motor control



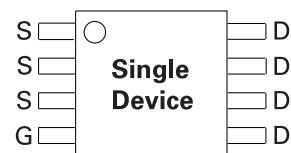
ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP3A16N8TA	7"	12mm	500 units
ZXMP3A16N8TC	13"	12mm	2500 units

DEVICE MARKING

- ZXMP
3A16

PINOUT



Top View

ZXMP3A16N8

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=-10V$; $T_A=25^\circ C$ (b) $V_{GS}=-10V$; $T_A=70^\circ C$ (b) $V_{GS}=-10V$; $T_A=25^\circ C$ (a)	I_D	-6.7 -5.4 -5.6	A
Pulsed Drain Current (c)	I_{DM}	-26	A
Continuous Source Current (Body Diode) (b)	I_S	-3.2	A
Pulsed Source Current (Body Diode) (c)	I_{SM}	-26	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	1.9 15.2	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	2.8 22.4	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	65	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	45	$^\circ C/W$

NOTES

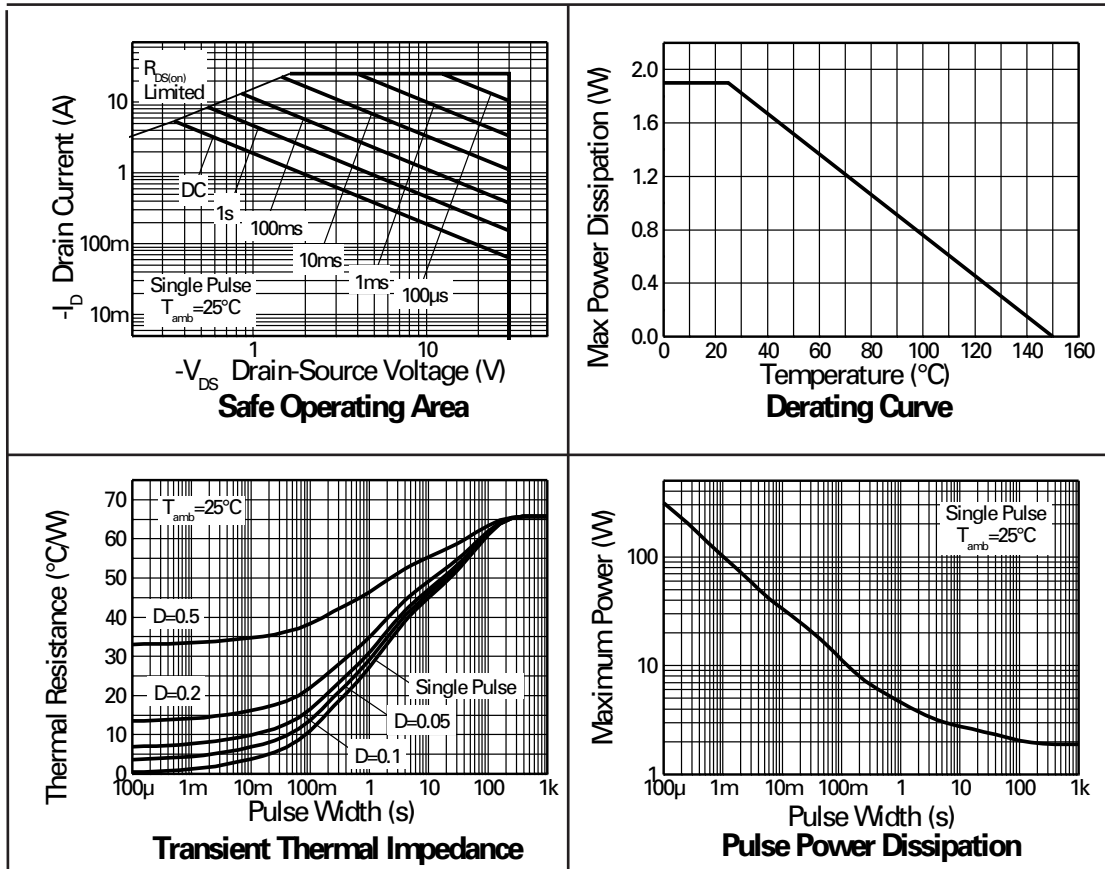
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.05$, pulse width 10 μs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

ZXMP3A16N8

CHARACTERISTICS



ZXMP3A16N8

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

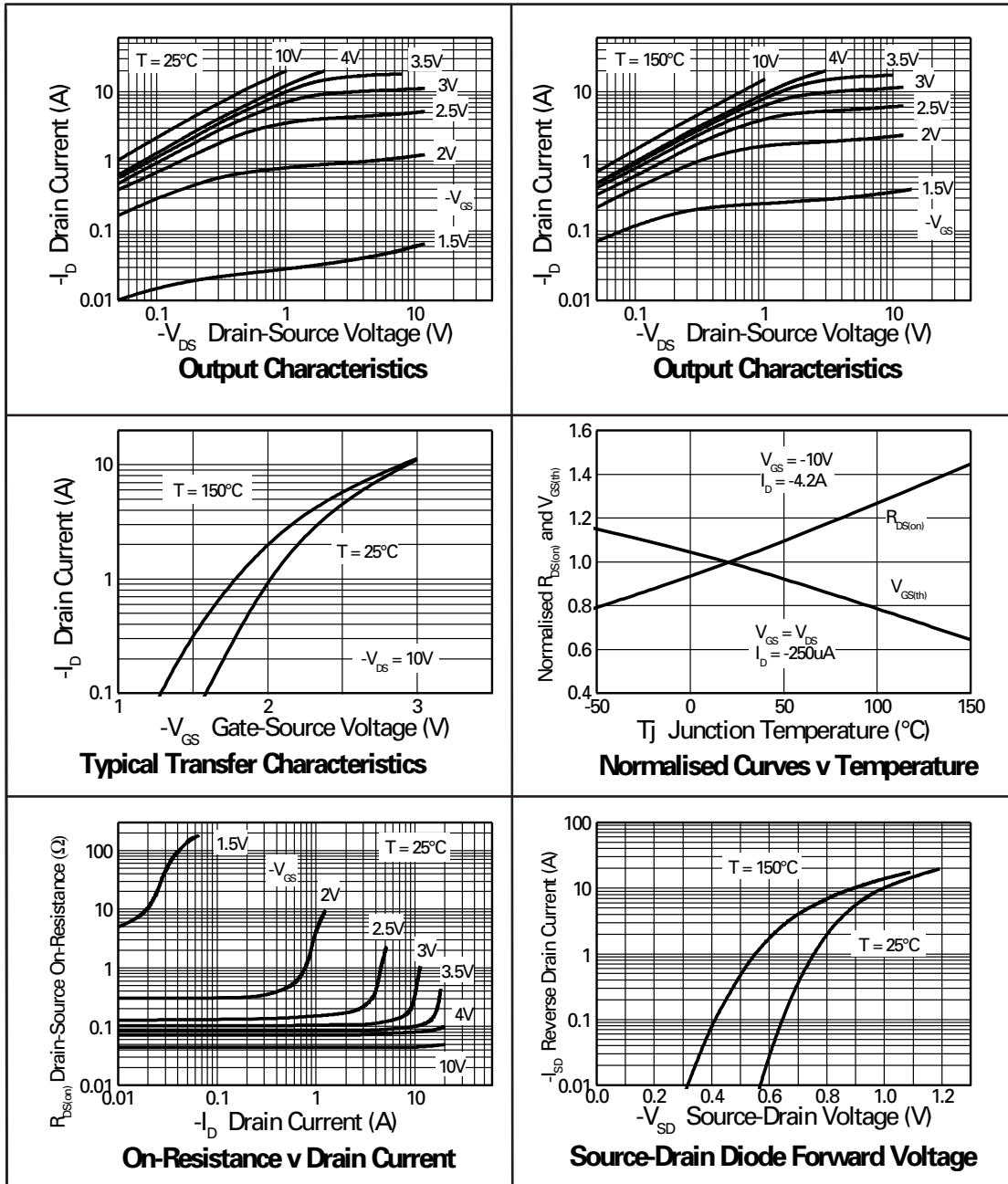
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	$I_D=-250\mu A, V_{GS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}			-1.0	μA	$V_{DS}=-30V, V_{GS}=0V$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D=-250\mu A, V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.040 0.070	Ω Ω	$V_{GS}=-10V, I_D=-4.2A$ $V_{GS}=-4.5V, I_D=-3.4A$
Forward Transconductance (1)(3)	g_{fs}		9.2		S	$V_{DS}=-15V, I_D=-4.2A$
DYNAMIC (3)						
Input Capacitance	C_{iss}		1022		pF	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$
Output Capacitance	C_{oss}		267		pF	
Reverse Transfer Capacitance	C_{rss}		229		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		3.8		ns	$V_{DD}=-15V, I_D=-1A$ $R_G=6.0\Omega, V_{GS}=-10V$
Rise Time	t_r		6.5		ns	
Turn-Off Delay Time	$t_{d(off)}$		37.1		ns	
Fall Time	t_f		21.4		ns	
Gate Charge	Q_g		17.2		nC	$V_{DS}=-15V, V_{GS}=-5V, I_D=-4.2A$
Total Gate Charge	Q_g		29.6		nC	$V_{DS}=-15V, V_{GS}=-10V, I_D=-4.2A$
Gate-Source Charge	Q_{gs}		2.8		nC	
Gate-Drain Charge	Q_{gd}		8.6		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}		-0.85	-0.95	V	$T_J=25^{\circ}C, I_S=-3.6A, V_{GS}=0V$
Reverse Recovery Time (3)	t_{rr}		21.7		ns	$T_J=25^{\circ}C, I_F=-2A, di/dt=100A/\mu s$
Reverse Recovery Charge (3)	Q_{rr}		16.1		nC	

NOTES

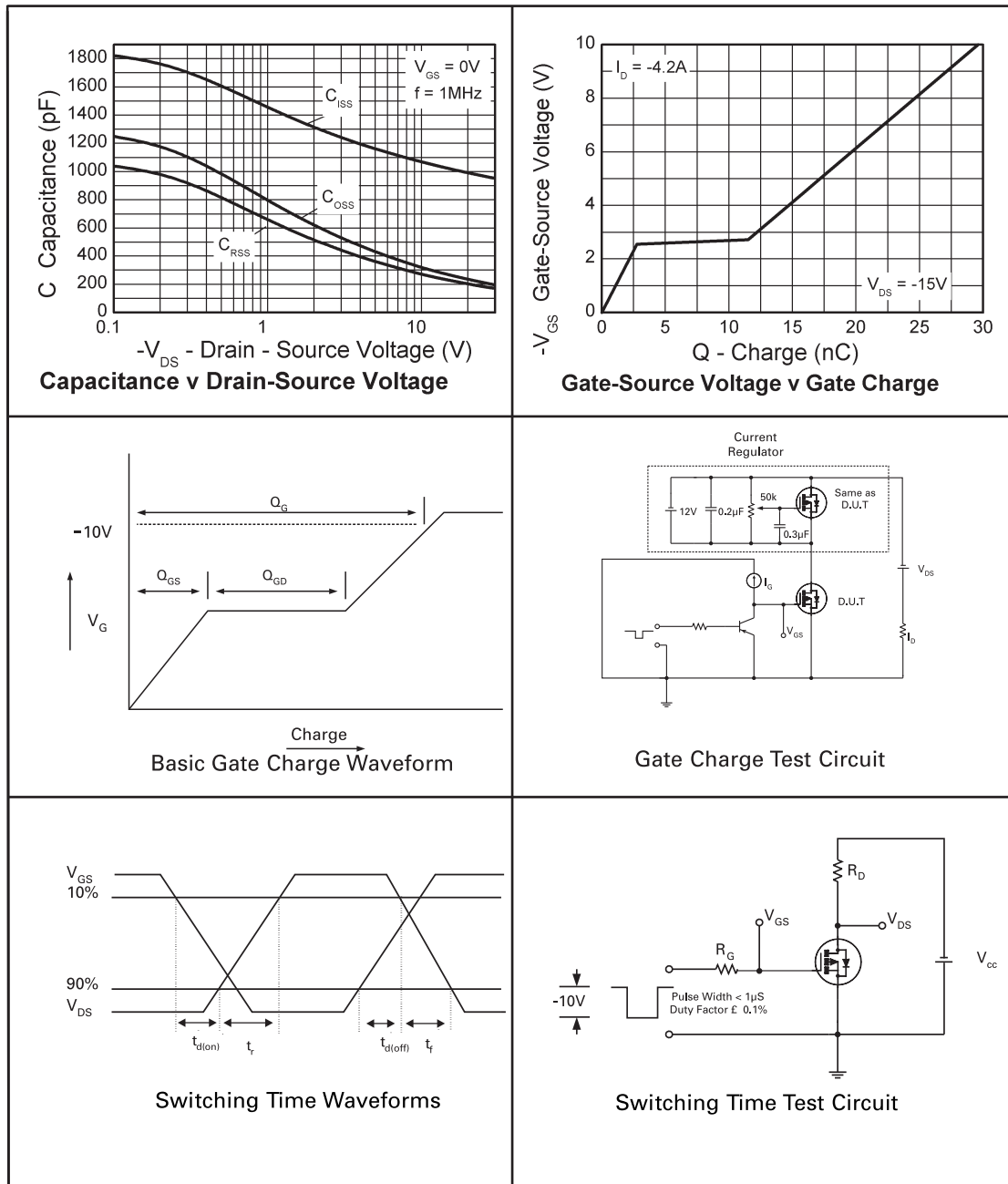
- (1) Measured under pulsed conditions. Width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

ZXMP3A16N8

CHARACTERISTICS



ZXMP3A16N8



ZXMP3A16N8

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"Not recommended for new designs"Device is still in production to support existing designs and production

"Obsolete"Production has been discontinued

Datasheet status key:

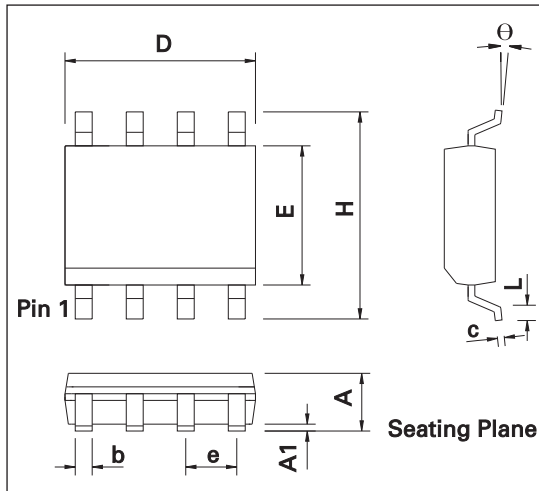
"Draft version" This term denotes a very early datasheet version and contains highly provisional information, which may change in any manner without notice.

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ZXMP3A16N8

PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES
APPROX IN MILLIMETERS

PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.35	1.75	0.053	0.069	e	1.27 BSC		0.050 BSC	
A1	0.10	0.25	0.004	0.010	b	0.33	0.51	0.013	0.020
D	4.80	5.00	0.189	0.197	c	0.19	0.25	0.008	0.010
H	5.80	6.20	0.228	0.244	Θ	0°	8°	0°	8°
E	3.80	4.00	0.150	0.157	h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050	-	-	-	-	-

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ISSUE 2 - MAY 2007